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PATENT

TECHNOLOGY CENTER 2800

Customer No. 22,852

Attorney Dock t No. 08038.0027

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Hikaru YOSHITAKA

Serial No.: 09/658,861

Filed: September 8, 2000

For: SEMICONDUCTOR DEVICE AND  
METHOD OF MANUFACTURING  
THE SAME

) Group Art Unit: 2812

) Examiner: Nguyen, H.

) VIA FACSIMILE @ (703) 308-7722

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

SUPPLEMENTAL AMENDMENT

In reply to a telephone conference with Examiner Nguyen on April 26, 2002,

Applicant hereby further amends the application as follows:

IN THE CLAIMS:

Please amend claim 4 as follows:

4. (Twice Amended) A method of manufacturing a semiconductor device, said  
method comprising the steps of:

forming a wiring layer on a semiconductor substrate having an active region

formed thereon;

forming a first insulating layer containing carbon on said wiring layer;